


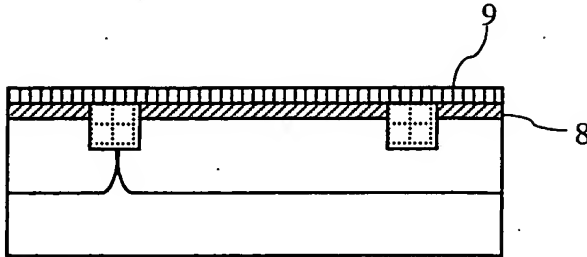
Fig. 1 is a cross-sectional view of a first embodiment of a semiconductor device. It shows a substrate 1 with a top layer 13. Two square regions 4 are embedded in the top layer 13, each containing a grid pattern.



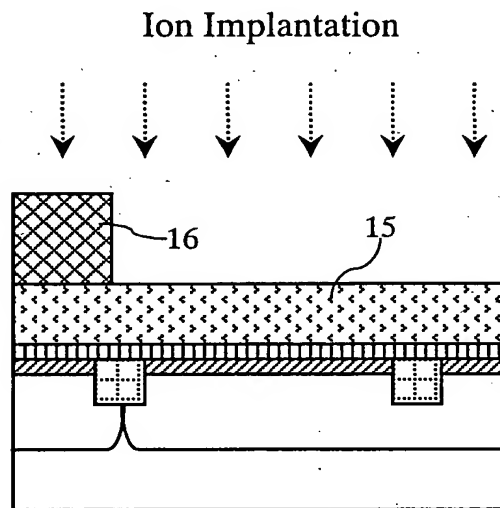
**Ion Implantation**

The diagram shows a cross-section of a substrate with a thin layer 14 on top. Six vertical arrows point downwards towards the layer 14, representing the ion implantation process.

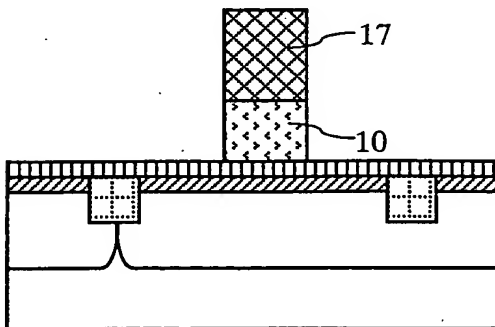
*Fig. 2D*



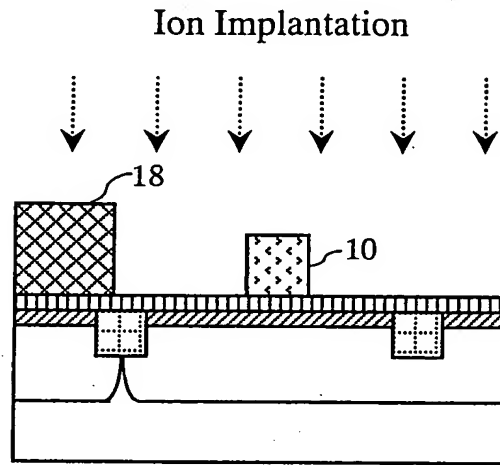
*Fig. 2E*



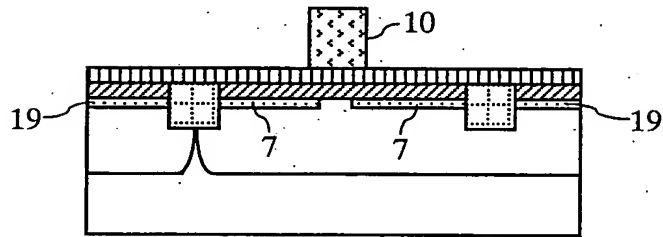
*Fig. 2F*



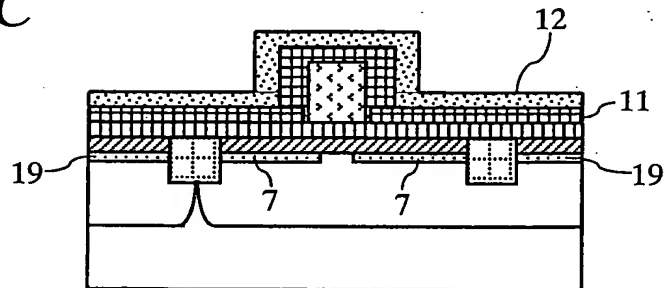
*Fig. 3A*



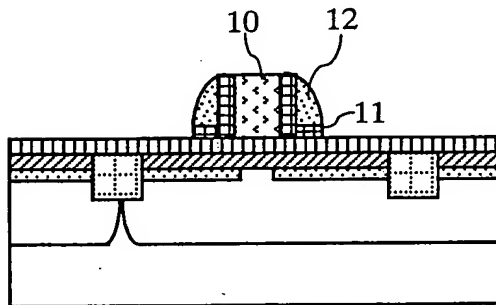
*Fig. 3B*



*Fig. 3C*

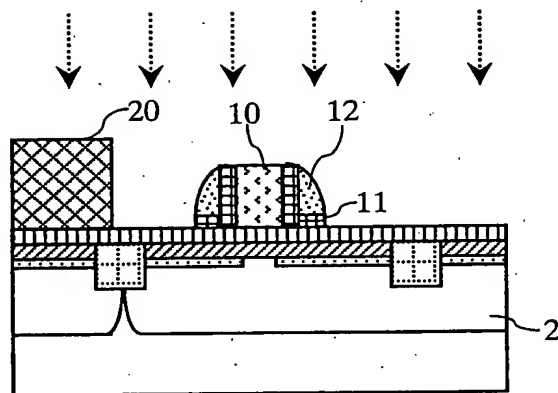


*Fig.3D*

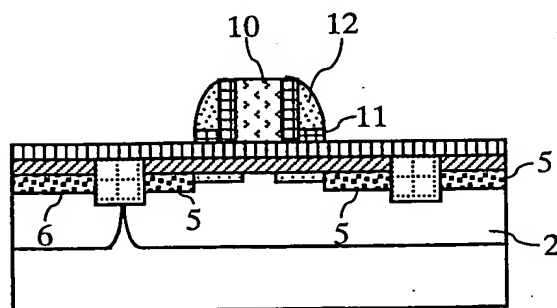


*Fig.3E*

Ion Implantation



*Fig.3F*



This cross-sectional view shows a semiconductor device with a central raised structure. The device is built on a substrate (1) with a layer (2) on top. A layer (3) is present on the left and right sides. The central structure consists of a raised portion (10) with a top layer (21) and a side layer (12). A layer (11) is located between the raised portion and the side layers. A layer (23) is on the top surface of the raised portion. A layer (22) is on the side surface of the raised portion. A layer (7) is on the bottom surface of the raised portion. A layer (6) is on the top surface of the side layers. A layer (5) is on the bottom surface of the side layers. A layer (4) is on the side surface of the side layers.

*Fig.5*

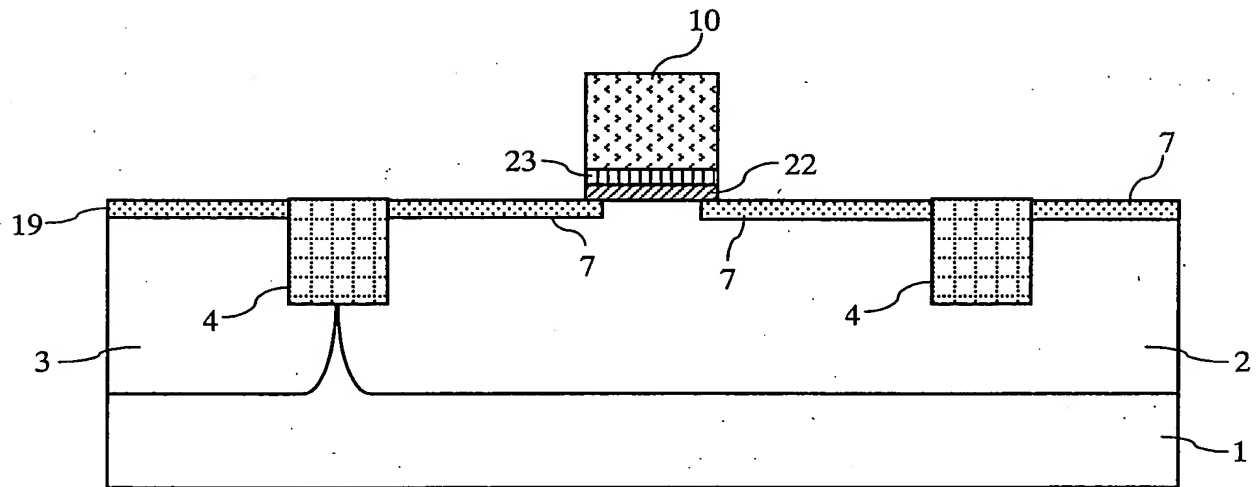
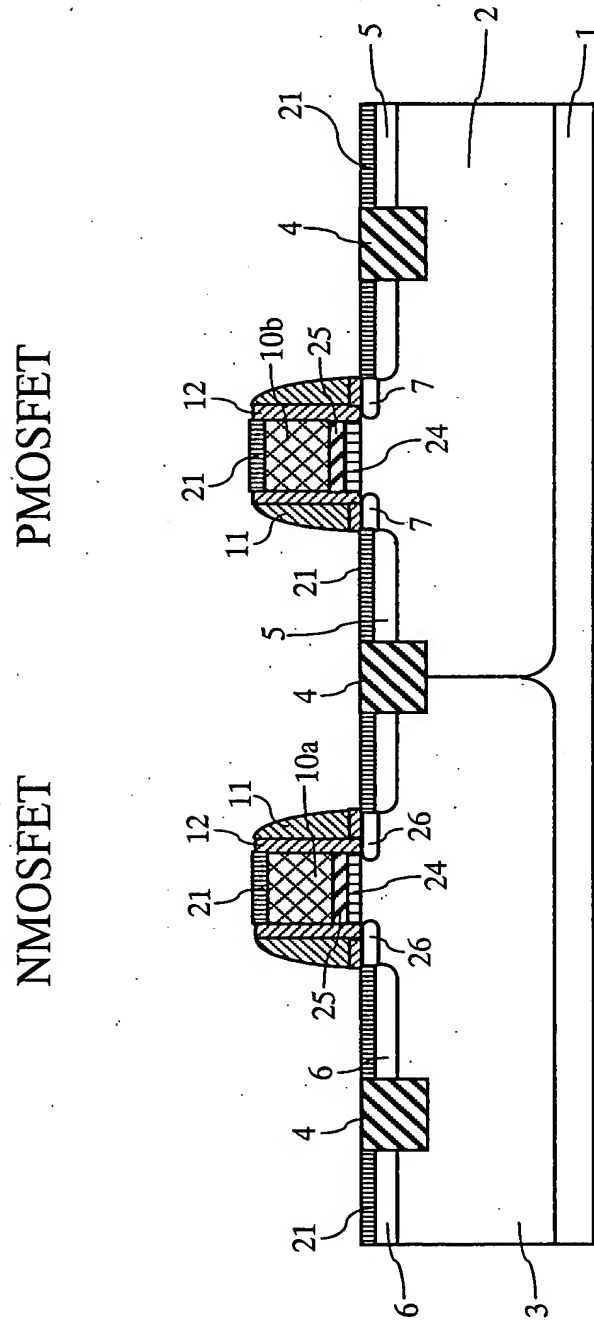


Fig. 6





*Fig. 7*

